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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Binghua Hu, et al. Docket No: TI-35362
Serial No: 10/712,455 Conf. No: 9290
Examiner: Laura M. Schillinger Art Unit: 2813
Filed: 11/12/2003
For: METHOD TO MANUFACTURE LDMOS TRANSISTORS WITH IMPROVED THRESHOLD VOLTAGE CONTROL

ELECTION

Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. § 1.8(a)
I hereby certify that the above correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 7-8-05.

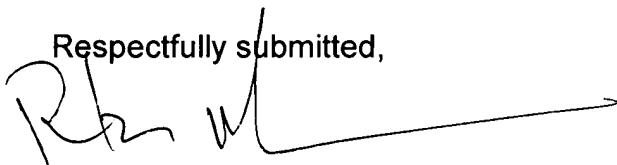
Ann Trent
Ann Trent

Dear Sir:

This election is offered in response to the Examiner's restriction requirement mailed June 21, 2005.

Applicants hereby elect to pursue Species 3 of Claims 8-10, pertaining to a method for forming LDMOS transistors including forming a deep n-well region and forming LOCOS isolation structures, without traversing the Examiner's restriction requirement.

Respectfully submitted,



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